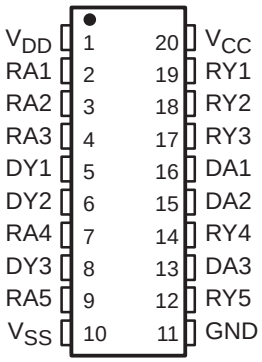
SLLS065F – AUGUST 1989 – REVISED JANUARY 2000

- **Meets or Exceeds the Requirements of TIA/EIA-232-F and ITU Recommendation V.28**
- **Single Chip With Easy Interface Between UART and Serial-Port Connector**
- **Less Than 9-mW Power Consumption**
- **Wide Driver Supply Voltage . . . 4.5 V to 13.2 V**
- **Driver Output Slew Rate Limited to 30 V/μs Max**
- **Receiver Input Hysteresis . . . 1100 mV Typ**
- **Push-Pull Receiver Outputs**
- **On-Chip Receiver 1-μs Noise Filter**
- **Functionally Interchangeable With Texas Instruments SN75185**
- **Operates Up to 120 kbit/s Over a 3-Meter Cable (See *Application Information* for Conditions)**

DW OR N PACKAGE
(TOP VIEW)



description

The SN75C185 is a low-power BiMOS device containing three independent drivers and five receivers that are used to interface data terminal equipment (DTE) with data circuit-terminating equipment (DCE). Typically, the SN75C185 replaces one SN75188 and two SN75189 devices. This device conforms to TIA/EIA-232-F. The drivers and receivers of the SN75C185 are similar to those of the SN75C188 and SN75C189A, respectively. The drivers have a controlled output slew rate that is limited to a maximum of 30 V/μs, and the receivers have filters that reject input noise pulses that are shorter than 1 μs. Both these features eliminate the need for external components.

The SN75C185 uses the low-power BiMOS technology. In most applications, the receivers contained in this device interface to single inputs of peripheral devices such as ACEs, UARTS, or microprocessors. By using sampling, such peripheral devices usually are insensitive to the transition times of the input signals. If this is not the case, or for other uses, it is recommended that the SN75C185 receiver outputs be buffered by single Schmitt input gates or single gates of the HCMOS, ALS, or 74F logic families.

The SN75C185 is characterized for operation from 0°C to 70°C.

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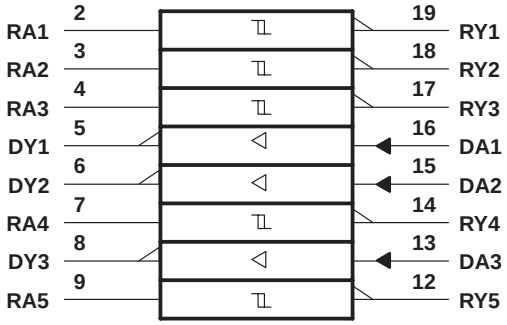
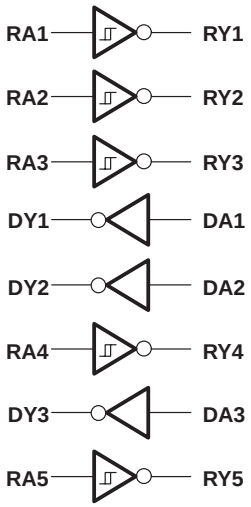
logic symbol†

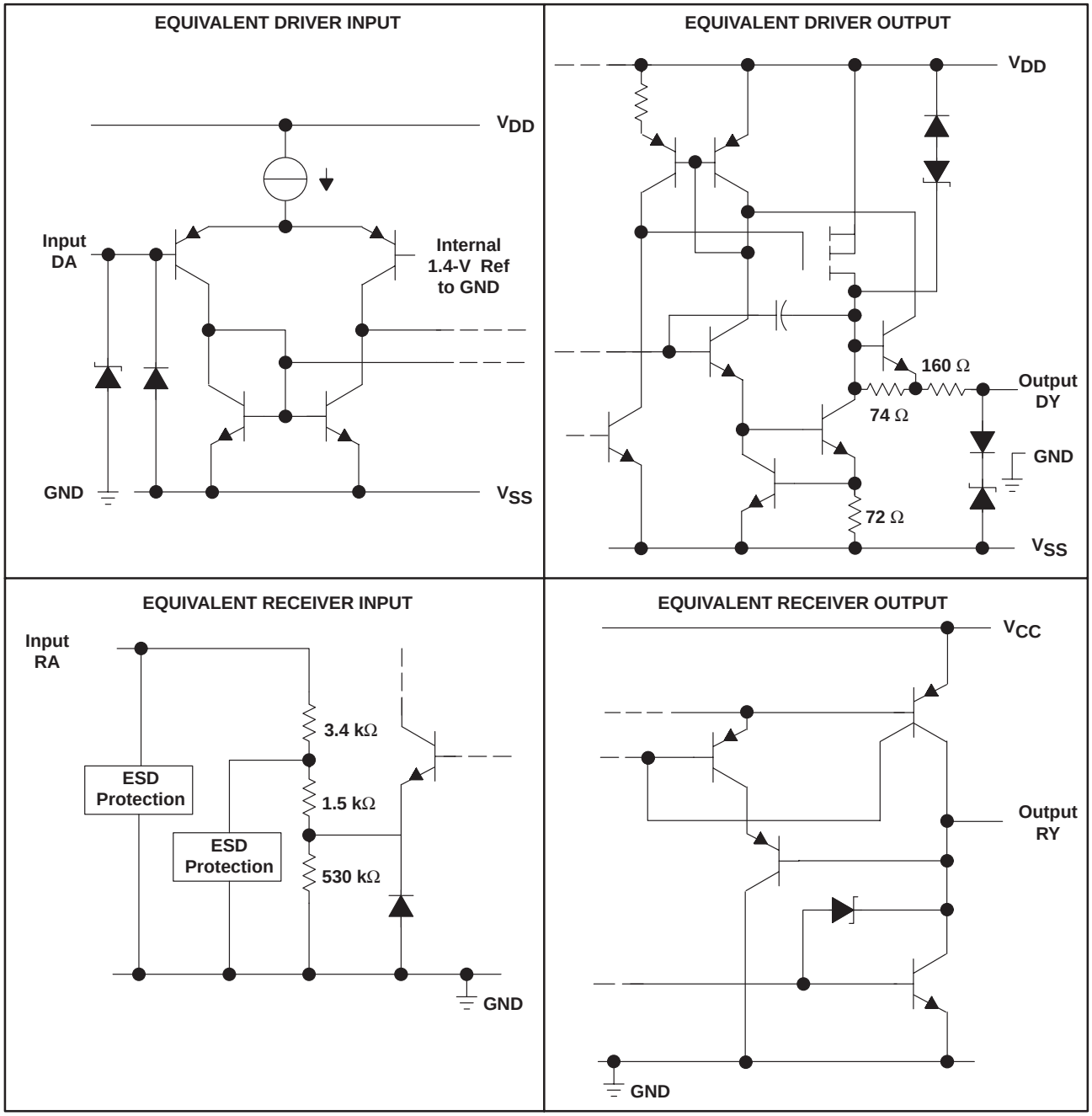


† This symbol is in accordance with ANSI/IEEE Std 91-1984 and IEC Publication 617-12.

logic diagram (positive logic)



equivalent schematics of inputs and outputs



All resistor values are nominal.

absolute maximum ratings over operating free-air temperature range (unless otherwise noted)†

Supply voltage, V_{DD} (see Note 1) . . . . . 13.5 V
Supply voltage, V_{SS} . . . . . –13.5 V
Supply voltage, V_{CC} . . . . . 7 V
Input voltage range, V_I: Driver . . . . . V_{SS} to V_{DD}
Receiver . . . . . –30 V to 30 V
Output voltage range, V_O: Driver . . . . . V_{SS} – 6 V to V_{DD} + 6 V
Receiver . . . . . –0.3 V to V_{CC} + 0.3 V
Package thermal impedance, θ_{JA} (see Note 2): DW package . . . . . 58°C/W
N package . . . . . 69°C/W
Operating free-air temperature range, T_A . . . . . 0°C to 70°C
Lead temperature 1,6 mm (1/16 inch) from case for 10 seconds . . . . . 260°C
Storage temperature range, T_{stg} . . . . . –65°C to 150°C

† Stresses beyond those listed under “absolute maximum ratings” may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under “recommended operating conditions” is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

NOTES: 1. All voltages are with respect to network GND.
2. The package thermal impedance is calculated in accordance with JESD 51.

recommended operating conditions

			MIN	NOM	MAX	UNIT
	Supply voltage	V_{DD}	4.5	12	13.2	V
		V_{SS}	–4.5	–12	–13.2	V
		V_{CC}	4.5	5	6	V
V_I	Input voltage (see Note 3)	Drivers	V_{SS}+2		V_{DD}	V
		Receivers	–25		25	
V_{IH}	High-level input voltage	Drivers	2			V
V_{IL}	Low-level input voltage				0.8	V
I_{OH}	High-level output current	Receivers			–1	mA
I_{OL}	High-level output current				3.2	mA
T_A	Operating free-air temperature		0		70	°C

NOTE 3: The algebraic convention, where the more positive (less negative) limit is designated as maximum, is used in this data sheet for logic levels only, e.g., if –10 V is a maximum, the typical value is a more negative voltage.

supply currents

PARAMETER		TEST CONDITIONS			MIN	TYP	MAX	UNIT
I_{DD}	Supply current from V_{DD}	No load, All inputs at 2 V or 0.8 V	V_{DD} = 5 V,	V_{SS} = –5 V		115	200	µA
			V_{DD} = 12 V,	V_{SS} = –12 V		115	200	
I_{SS}	Supply current from V_{SS}	No load, All inputs at 2 V or 0.8 V	V_{DD} = 5 V,	V_{SS} = –5 V		–115	–200	µA
			V_{DD} = 12 V,	V_{SS} = –12 V		–115	–200	
I_{CC}	Supply current from V_{CC}	No load All inputs at 0 or 5 V	V_{DD} = 5 V,	V_{SS} = –5 V			750	µA
			V_{DD} = 12 V,	V_{SS} = –12 V			750	

DRIVER SECTION

electrical characteristics over operating free-air temperature range, V_{DD} = 12 V, V_{SS} = –12 V, V_{CC} = 5 V ±10% (unless otherwise noted)

PARAMETER		TEST CONDITIONS			MIN	TYP†	MAX	UNIT
V_{OH}	High-level output voltage	V_{IL} = 0.8 V, See Figure 1	R_L = 3 kΩ,	V_{DD} = 5 V, V_{SS} = –5 V	4	4.5		V
				V_{DD} = 12 V V_{SS} = –12 V	10	10.8		
V_{OL}	Low-level output voltage (see Note 3)	V_{IH} = 0.8 V, See Figure 1	R_L = 3 kΩ,	V_{DD} = 5 V, V_{SS} = –5 V		–4.4	–4	V
				V_{DD} = 12 V V_{SS} = –12 V		–10.7	–10	
I_{IH}	High-level input current	V_I = 5 V,	See Figure 2				1	µA
I_{IL}	Low-level input current	V_I = 0,	See Figure 2				–1	µA
$I_{OS(H)}$	High-level short-circuit output current (see Note 4)	V_I = 0.8 V, See FIgure 1	V_O = 0 or V_O = V_{SS},		–4.5	–12	–19.5	mA
$I_{OS(L)}$	Low-level short-circuit output current (see Note 4)	V_I = 2 V, See Figure 1	V_O = 0 or V_O = V_{DD},		4.5	12	19.5	mA
r_o	Output resistance	V_{DD} = V_{SS} = V_{CC} = 0, See Note 5	V_O = – 2 V to 2 V,		300	400		Ω

† All typical values are at T_A = 25°C.

NOTES: 3. The algebraic convention, where the more positive (less negative) limit is designated as maximum, is used in this data sheet for logic levels only, e.g., if –10 V is a maximum, the typical value is a more negative voltage.
4. Not more than one output should be shorted at one time.
5. Test conditions are those specified by TIA/EIA-232-F.

switching characteristics, V_{DD} = 12 V, V_{SS} = –12 V, V_{CC} = 5 V ±10%, T_A = 25°C (unless otherwise noted) (see Figure 3)

PARAMETER		TEST CONDITIONS		MIN	TYP	MAX	UNIT
t_{PLH}	Propagation delay time, low- to high-level output (see Note 6)	R_L = 3 kΩ to 7 kΩ,	C_L = 15 pF		1.2	3	µs
t_{PHL}	Propagation delay time, high- to low-level output (see Note 6)				2.5	3.5	µs
t_{TLH}	Transition time, low- to high-level output			0.53	2	3.2	µs
t_{THL}	Transition time, high- to low-level output			0.53	2	3.2	µs
t_{TLH}	Transition time, low- to high-level output (see Note 7)	R_L = 3 kΩ to 7 kΩ,	C_L = 2500 pF		1		µs
t_{THL}	Transition time, high- to low-level output (see Note 7)				1		µs
S_R	Output slew rate (see Note 7)	R_L = 3 kΩ to 7 kΩ,	C_L = 15 pF	4	10	30	V/µs

NOTES: 6. t_{PHL} and t_{PLH} include the additional time due to on-chip slew rate and are measured at the 50% points.
7. Measured between 3-V and –3-V points of output waveform TIA/EIA-232-F conditions), and all unused inputs are tied either high or low.

RECEIVER SECTION

electrical characteristics over operating free-air temperature range, V_{DD} = 12 V, V_{SS} = −12 V, V_{CC} = 5 V ±10% (unless otherwise noted)

PARAMETER		TEST CONDITIONS			MIN	TYP†	MAX	UNIT
V_{IT+}	Positive-going input threshhold voltage	See Figure 5			1.6	2.1	2.55	V
V_{IT-}	Negative-going input threshhold voltage	See Figure 5			0.65	1	1.25	V
V_{hys}	Input hysteresis voltage ($V_{IT+} - V_{IT-}$)				600	1100		mV
V_{OH}	High-level output voltage	V_I = 0.75 V,	I_{OH} = −20 µA,	See Figure 5 and Note 8	3.5			V
		V_I = 0.75 V, I_{OH} = −1 mA, See Figure 5	V_{CC} = 4.5 V		2.8	4.4		
			V_{CC} = 5 V		3.8	4.9		
			V_{CC} = 5.5 V		4.3	5.4		
V_{OL}	Low-level output voltage	V_I = 3 V,	I_{OL} = 3.2 mA,	See Figure 5		0.17	0.4	V
I_{IH}	High-level input current	V_I = 3 V			0.43	0.55	1	mA
		V_I = 25 V			3.6	4.6	8.3	
I_{IL}	Low-level input current	V_I = −3 V			−0.43	−0.55	−1	mA
		V_I = −25 V			−3.6	−5.0	−8.3	
$I_{OS(H)}$	Short-circuit output at high level	V_I = 0.75 V,	V_O = 0,	See Figure 4		−8	−15	mA
$I_{OS(L)}$	Short-circuit output at low level	V_I = V_{CC},	V_O = V_{CC},	See Figure 4		13	25	mA

† All typical values are at T_A = 25°C.

NOTE 8: If the inputs are left unconnected, the receiver interprets this as an input low, and the receiver outputs remain in the high state.

switching characteristics, V_{DD} = 12 V, V_{SS} = −12 V, V_{CC} = 5 V ±10%, T_A = 25°C (unless otherwise noted) (see Figure 6)

PARAMETER		TEST CONDITIONS		MIN	TYP	MAX	UNIT
t_{PLH}	Propagation delay time, low- to high-level output	R_L = 5 kΩ,	C_L = 50 pF		3	4	µs
t_{PHL}	Propagation delay time, high- to low-level output				3	4	µs
t_{TLH}	Transition time, low- to high-level output				300	450	ns
t_{THL}	Transition time, high- to low-level output				100	300	ns
$t_{w(N)}$	Duration of longest pulse rejected as noise (see Note 9)	R_L = 5 kΩ,	C_L = 50 pF	1		4	µs

NOTE 9: The receiver ignores any postive- or negative-going pulse that is less than the minimum value of $t_{w(N)}$ and accepts any positive- or negative-going pulse greater than the maximum of $t_{w(N)}$.

PARAMETER MEASUREMENT INFORMATION

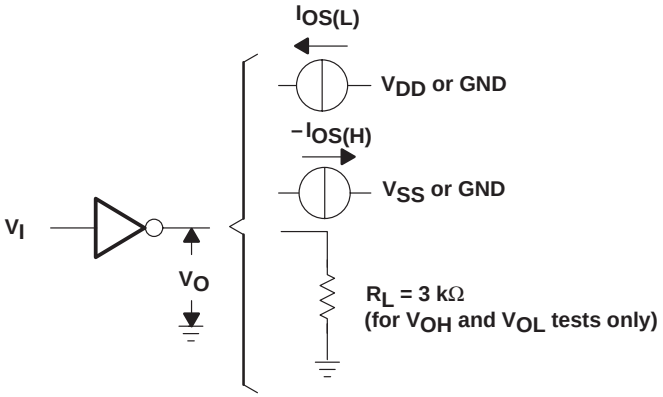


Figure 1. Driver Test Circuit for V_{OH}, V_{OL}, $I_{OS(H)}$, and $I_{OS(L)}$

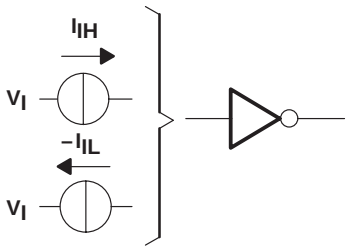
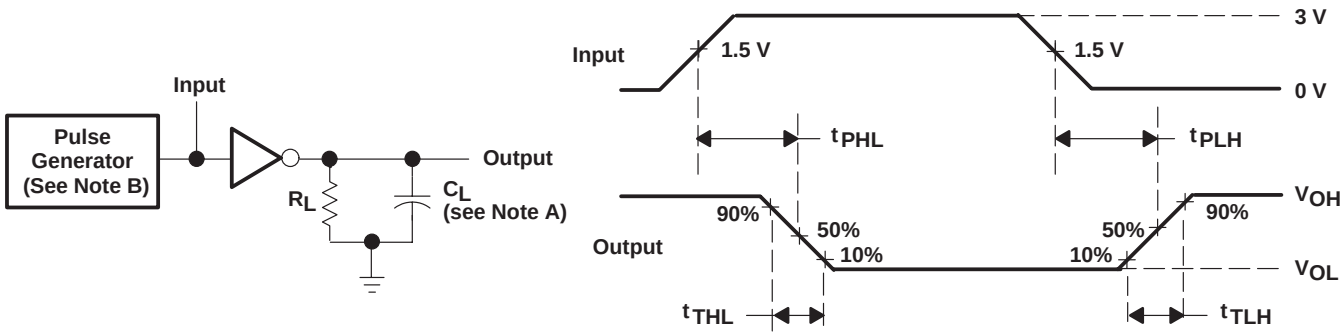


Figure 2. Driver Test Circuit for I_{IH} and I_{IL}



NOTES: A. C_L includes probe and jig capacitance.
B. The pulse generator has the following characteristics: t_W = 25 μs, PRR = 20 kHz, Z_O = 50 Ω, $t_r = t_f$ < 50 ns.

Figure 3. Driver Test Circuit and Voltage Waveforms

PARAMETER MEASUREMENT INFORMATION

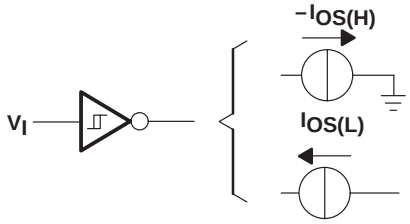


Figure 4. Receiver Test Circuit for $I_{OS(H)}$ and $I_{OS(L)}$

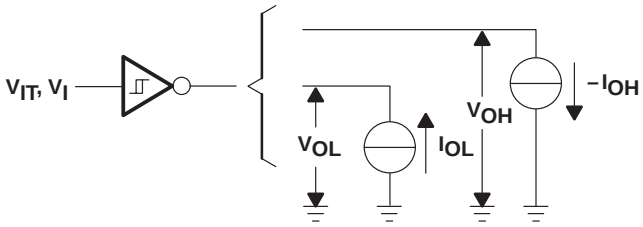
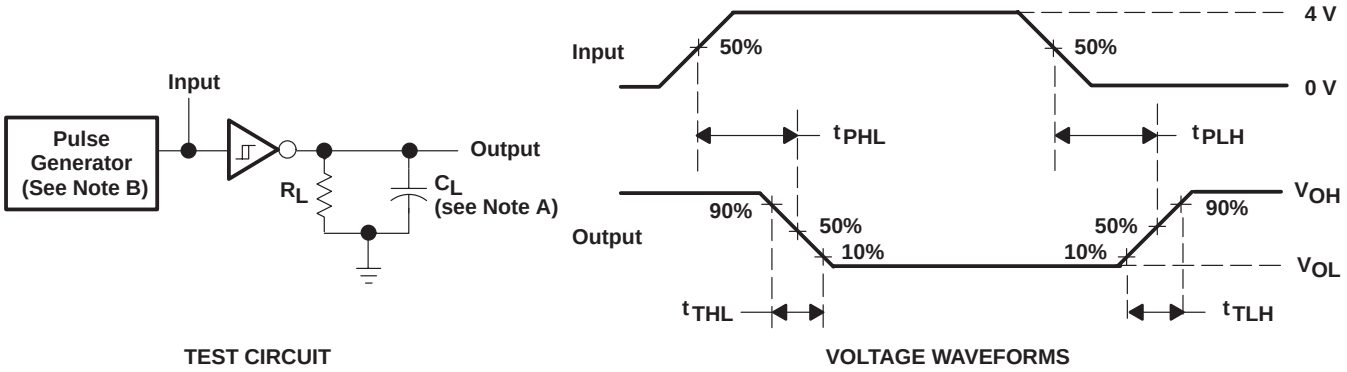


Figure 5. Receiver Test Circuit for V_{IT}, V_{OH}, and V_{OL}



NOTES: A. C_L includes probe and jig capacitance.
B. The pulse generator has the following characteristics: t_w = 25 µs, PRR = 20 kHz, Z_O = 50 Ω, $t_r = t_f$ < 50 ns.

Figure 6. Receiver Propagation and Transition Times

APPLICATION INFORMATION

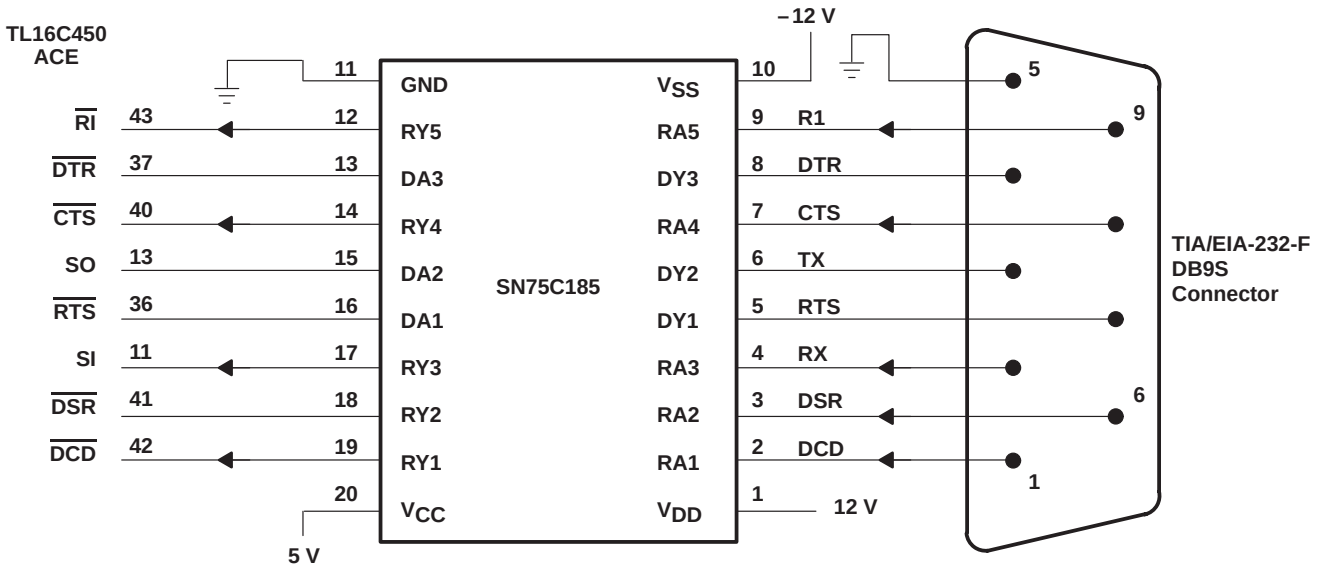
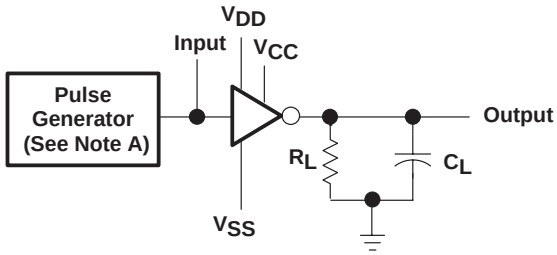


Figure 7. Typical Connection

The SN75C185 supports data rates up to 120 kbit/s over a 3-meter cable. Laboratory experiments show that, with C_L = 500 pF and R_L = 3 kΩ (minimum RS-232 input resistance load), the device can support this data rate. The 500-pF load approximates a typical 3-meter cable because the maximum RS-232 specification is 2500 pF (or about 15 meters). Figure 8 shows the test circuit used. Temperature was varied from 0°C to 70°C for the experiment.



NOTES: A. The pulse generator has the following characteristics: PRR = 60 kHz (120 kbit/s), Z_O = 50 Ω.
B. V_{CC} = 5 V, V_{DD} = 12 V, V_{SS} = –12 V.

Figure 8. Data-Rate Test Circuit

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